

USB 3.0 Single Channel Redriver with Equalization

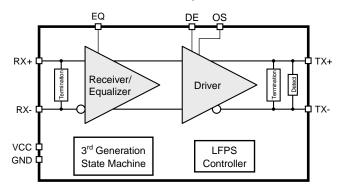
Check for Samples: TUSB501

FEATURES

- Aggressive Low-Power Architecture (Typ):
 - 126 mW Active Power
 - 20 mW in U2/U3
 - 3 mW with No Connection
- Automatic LFPS DE Control
- Excellent Jitter and Loss Compensation
 - 32 inches of FR4 4 mil Stripline
 - 3 m of 30 AWG cable
- Integrated Termination
- Small 2 x 2 mm QFN Package
- Selectable Receiver Equalization, Transmitter De-Emphasis and Output Swing
- Hot-Plug Capable
- ESD Protection ±5 kV HBM

APPLICATIONS

 Cell Phones, Computers, Docking Stations, TVs, Active Cables, Backplanes



DESCRIPTION

The TUSB501 is a 3rd generation 3.3-V USB 3.0 single-channel redriver. When 5 Gbps SuperSpeed USB signals travel across a PCB or cable, signal integrity degrades due to loss and inter-symbol interference. The TUSB501 recovers incoming data by applying equalization that compensates channel loss, and drives out signals with a high differential voltage. This extends the possible channel length, and enables systems to pass USB 3.0 compliance. The TUSB501 advanced state machine makes it transparent to hosts and devices.

After power up, the TUSB501 periodically performs receiver detection on the TX pair. If it detects a SuperSpeed USB receiver, RX termination becomes enabled, and the TUSB501 is ready to redrive.

The receiver equalizer has three gain settings that are controlled by pin EQ: 3 dB, 6 dB, and 9 dB. This should be set based on amount of loss before the TUSB501. Likewise, the output driver supports configuration of De-Emphasis and Output Swing (pins DE and OS). These settings allow the TUSB501 to be flexibly placed in the SuperSpeed USB path, with optimal performance.

Over previous generations, the TUSB501 features reduced power in all link states, a stronger OS option, improved receiver equalization settings, and an intelligent LFPS Controller. This controller senses the low frequency signals and automatically disables driver de-emphasis, for full USB 3.0 compliance.

The TUSB501 is packaged in a small 2 x 2 mm QFN, and operates through an industrial temperature range of -40° C to 85° C.

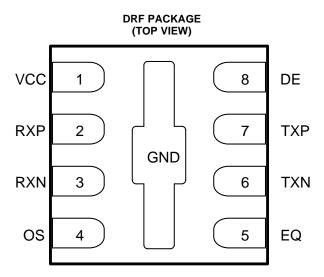
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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



PIN FUNCTIONS

F	PIN		PIN TYPE		DESCRIPTION		
NAME	NO.	ITPE	DESCRIPTION				
RXP	2		Differential input pair for F. Chap. Conservand LICD singula				
RXN	3	D:#+i1.1/O	Differential input pair for 5 Gbps SuperSpeed USB signals.				
TXN	6	Differential I/O	Differential output pair for E Chan Cunar Chand LICE signals				
TXP	7		Differential output pair for 5 Gbps SuperSpeed USB signals.				
EQ	5		Sets the receiver equalizer gain. 3-state input with integrated pull-up and pull-down resistors.				
DE	8	CMOS Input	Sets the output de-emphasis gain. 3-state input with integrated pull-up and pull-down resistors.				
os	4		Sets the output swing (differential voltage amplitude). 2-state input with an integrated pull-down resistor.				
VCC	1	Dower	3.3-V power supply				
GND	Thermal Pad	Power	Reference ground				



DEVICE CONFIGURATION

Table 1. Control Pin Effects (Typical Values)

PIN	DESCRIPTION	LOGIC STATE	GAIN
		Low	3 dB
EQ	Equalization Amount	Floating	6 dB
		High	9 dB

PIN	DESCRIPTION	LOGIC STATE	OUTPUT DIFFERENTIAL VOLTAGE FOR THE TRANSITION BIT
os	Output Swing	Low	930 mV _{pp}
US	Amplitude	High	1300 mV _{pp}

PIN	DESCRIPTION	LOGIC STATE	DE-EMPHASIS RATIO		
	DESCRIPTION	LOGIC STATE	FOR OS = LOW	FOR OS = HIGH	
		Low	0 dB	–2.6 dB	
DE	De-Emphasis Amount	Floating	−3.5 dB	−5.9 dB	
	, anount	High	−6.2 dB	-8.3 dB	

⁽¹⁾ Typical values

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT	
Supply voltage range (2)	V _{CC}	-0.5	4	V	
Voltage range at any input or output terminal	Differential I/O	-0.5	4	V	
	CMOS inputs	-0.5	$V_{CC} + 0.5$	V	
	Human body model (all pins) (3)		±5	1-1/	
Electrostatic discharge	Charged-device model (all pins) (4)			kV	
Storage temperature, T _{STG}			150	°C	
Maximum junction temperature, T _J			105	°C	

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

	TUEDMAL METDIO(1)	TUSB501 DRF 102.4 90.3 21.2 70 3.6	
	THERMAL METRIC ⁽¹⁾	DRF	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	102.4	
$\theta_{JC(top)}$	Junction-to-case(top) thermal resistance	90.3	
θ_{JB}	Junction-to-board thermal resistance	21.2	900
ΨЈТ	Junction-to-top characterization parameter	70	°C/W
ΨЈВ	Junction-to-board characterization parameter	3.6	
$\theta_{JC(bottom)}$	Junction-to-case(bottom) thermal resistance	70.2	

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

⁽²⁾ All voltage values are with respect to the GND terminals.

⁽³⁾ Tested in accordance with JEDEC Standard 22, Test Method A114-B.

⁽⁴⁾ Tested in accordance with JEDEC Standard 22, Test Method C101-A.



RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Main power supply	3	3.3	3.6	V
T _A	Operating free-air temperature	-40		85	°C
C _{AC}	AC coupling capacitor	75	100	200	nF

POWER SUPPLY CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX ⁽²⁾	UNIT	
I _{CC-ACTIVE}	Average estive current	Link in U0 with SuperSpeed USB data transmission, OS = Low		38.1		A	
	Average active current	Link in U0 with SuperSpeed USB data transmission, OS = High		43.8	65	mA	
I _{CC-IDLE}	Average current in idle state	Link has some activity, not in U0, OS = Low		29.8		mA	
I _{CC-U2U3}	Average current in U2/U3	Link in U2 or U3		6.1		mA	
I _{CC-NC}	Average current with no connection	No SuperSpeed USB device is connected to TXP, TXN		1.3		mA	
D	Bower Discipation in LIO	OS = Low		126		\/	
P_D	Power Dissipation in U0	OS = High		145	234	mW	

DC ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
3-State	CMOS Inputs (EQ, DE)				
V _{IH}	High-level input voltage		2.8		V
V _{IM}	Mid-level input voltage		V _{CC} / 2		V
V _{IL}	Low-level input voltage			0.6	V
V _F	Floating voltage	V _{IN} = High impedance	V _{CC} / 2		V
R _{PU}	Internal pull-up resistance		190		kΩ
R _{PD}	Internal pull-down resistance		190		kΩ
I _{IH}	High-level input current	V _{IN} = 3.6 V		36	μΑ
I _{IL}	Low-level input current	$V_{IN} = GND, V_{CC} = 3.6 \text{ V}$	-36		μΑ
2-State	CMOS Input (OS)				
V _{IH}	High-level input voltage		2		V
V _{IL}	Low-level input voltage			0.5	V
V _F	Floating voltage	V _{IN} = High impedance	GND		V
R _{PD}	Internal pull-down resistance		270		kΩ
I _{IH}	High-level input current	V _{IN} = 3.6 V		26	μΑ
I _{IL}	Low-level input current	V _{IN} = GND	-1		μA

 $[\]begin{array}{ll} \hbox{(1)} & \hbox{TYP values use V}_{CC} = 3.3 \ \hbox{V, T}_{A} = 25 ^{\circ} \hbox{C.} \\ \hbox{(2)} & \hbox{MAX values use V}_{CC} = 3.6 \ \hbox{V, T}_{A} = -40 ^{\circ} \hbox{C.} \\ \end{array}$



AC ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Differential	Receiver (RXP, RXN)				•	
V _{DIFF-pp}	Input differential voltage swing	AC-coupled differential peak-to-peak signal	100		1200	mV_{pp}
V _{CM-RX}	Common-mode voltage bias in the receiver (DC)			3.3		V
Z _{RX-DIFF}	Differential input impedance (DC)	Present after a SuperSpeed USB device is detected on TXP/TXN	72	91	120	Ω
Z _{RX-CM}	Common-mode input impedance (DC)	Present after a SuperSpeed USB device is detected on TXP, TXN	18	22.8	30	Ω
Z _{RX-HIGH-} IMP-DC-POS	Common-mode input impedance with termination disabled (DC)	Present when no SuperSpeed USB device is detected on TXP, TXN. Measured over the range of 0-500 mV with respect to GND.	25	25 35		kΩ
V _{RX-LFPS-} DET-DIFF-pp	Low Frequency Periodic Signaling (LFPS) Detect Threshold	Below the minimum is squelched	100		300	mV_pp
Differential	Transmitter (TXP, TXN)					
\ /	Transmitter differential voltage swing	OS = Low, No load		930		mV _{pp} mV _{pp} dB pF 25 Ω 00 mA 50 mA 70 mV _{pp} mV _{pp} mV _{pp} mV _{pp} mV _{pp}
V _{TX-DIFF-PP}	(transition-bit)	OS = High, No load		1300		
V _{TX-DE-}	Transmitter de-emphasis	DE = Floating, OS = Low		-3.5		dB
C _{TX}	TX input capacitance to GND	At 2.5 GHz 1.25		1.25		pF
Z _{TX-DIFF}	Differential impedance of the driver		75 93 125		125	Ω
Z _{TX-CM}	Common-mode impedance of the driver	Measured with respect to AC ground over 0-500 mV	18.75 31.29		31.25	Ω
I _{TX-SC}	TX short circuit current	TX ± shorted to GND			60	mA
V _{CM-TX}	Common-mode voltage bias in the transmitter (DC)		1.2		2.5	V
V _{CM-TX-AC}	AC common-mode voltage swing in active mode	Within U0 and within LFPS			100	mV_{pp}
V _{TX-IDLE-} DIFF -AC-pp	Differential voltage swing during electrical idle	Tested with a high-pass filter	0		10	mV_pp
V _{TX-CM-} DeltaU1-U0	Absolute delta of DC CM voltage during active and idle states	Restrict the test condition to meet 100 mV			100	mV
V _{TX-idle-diff-} DC	DC electrical idle differential output voltage	Voltage must be low pass filtered to remove any AC component	0		12	mV
Differential	Transmitter (TXP, TXN)					
t _R , t _F	Output rise, fall time see Figure 4	20%-80% of differential voltage measured 1 inch from the output pin		80		ps
t _{RF-MM}	Output Rise, Fall time mismatch	20%-80% of differential voltage measured 1 inch from the output pin			20	ps
t _{diff-LH} , t _{diff-HL}	Differential propagation delay see Figure 2	De-emphasis = -3.5 dB propagation delay between 50% level at input and output		290		ps
t _{idleEntry} , t _{idleExit}	Idle entry and exit times see Figure 3			3.6		ns



AC ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER TEST CONDITIONS		MIN	TYP	MAX	UNIT	
Timing							
t _{READY}	Time from power applied until RX termination	Apply 0 V to VCC, connect SuperSpeed USB termination to TX±, apply 3.3 V to VCC, and measure when Z _{RX-DIFF} is enabled.		9		ms	
Jitter							
T _{JTX-EYE}	Total jitter (1) (2)	EQ = Floating, OS = High,		0.213		UI ⁽³⁾	
D _{JTX}	Deterministic jitter (2)	DE = High		0.197		UI ⁽³⁾	
R _{JTX}	Random jitter (2) (4)	See Figure 1.	0.016			UI ⁽³⁾	

- Includes R_J at 10⁻¹².
- Measured at the ends of reference channel in Figure 1 with K28.5 pattern, V_{ID} = 1000 m V_{pp} , 5 Gbps, -3.5 dB de-emphasis from source.
- UI = 200 ps.
- (3) (4) R_i calculated as 14.069 times the RMS random jitter for 10⁻¹² BER.

PARAMETER MEASUREMENT INFORMATION

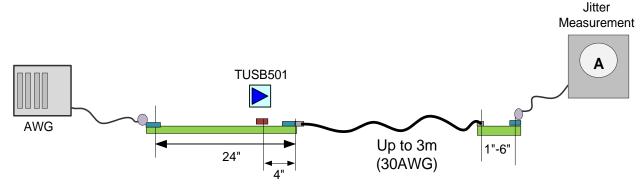


Figure 1. Jitter Measurement Setup

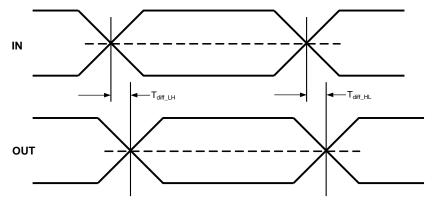


Figure 2. Propagation Delay

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PARAMETER MEASUREMENT INFORMATION (continued)

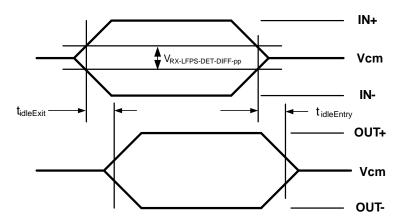


Figure 3. Electrical Idle Mode Exit and Entry Delay

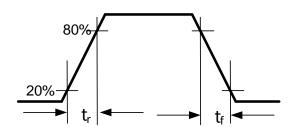


Figure 4. Output Rise and Fall Times

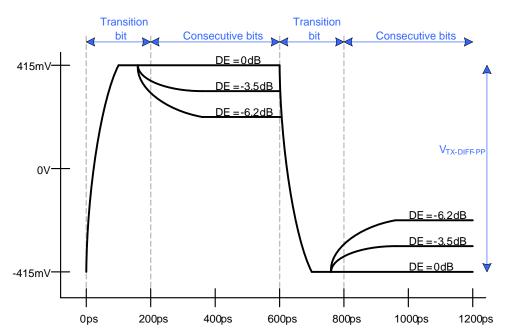


Figure 5. Transmitter Differential Voltage, OS = L

PARAMETER MEASUREMENT INFORMATION (continued)

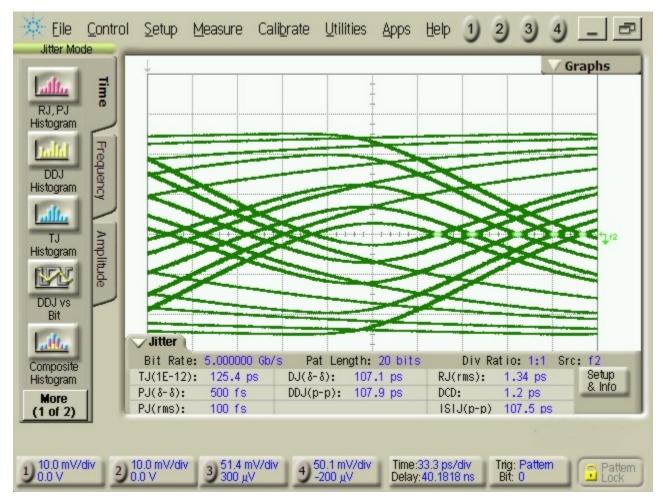


Figure 6. Input for Typical Output Measurement at TUSB501 at $T_A = 25^{\circ}C$



PARAMETER MEASUREMENT INFORMATION (continued)

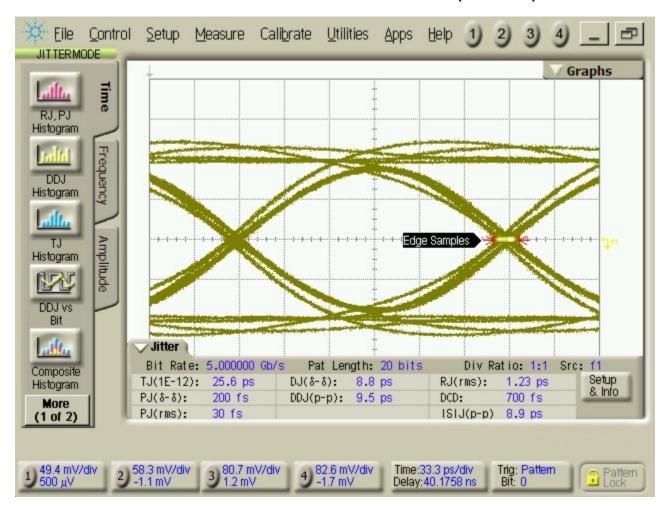


Figure 7. Typical Output Eye for Jitter Measurement Setup in Figure 1 at $T_A = 25^{\circ}$ C, DE = HIGH, OS = HIGH, EQ = NC

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•	Changed from Product Preview to Production Data	1



PACKAGE OPTION ADDENDUM

14-Aug-2013

PACKAGING INFORMATION

Orderable Device Status		Package Type	ackage Type Package Pi		•		Lead/Ball Finish MSL Peak Temp		Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
TUSB501DRFR	ACTIVE	WSON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	T501	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TUSB501DRFR	WSON	DRF	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

PACKAGE MATERIALS INFORMATION

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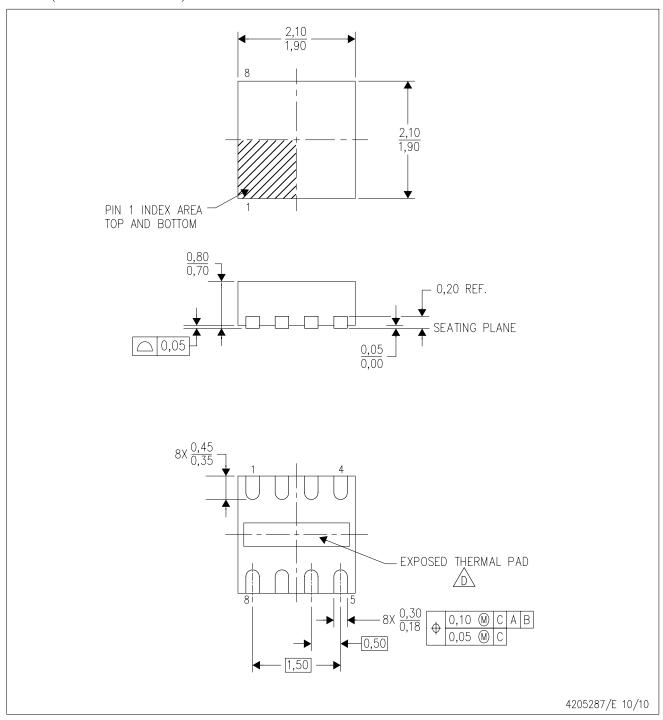


*All dimensions are nominal

Ī	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
	TUSB501DRFR	WSON	DRF	8	3000	210.0	185.0	35.0	

DRF (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- Ç. Quad Flatpack, No-Leads (QFN) package configuration.
- The Package thermal pad must be soldered to the board for thermal and mechanical performance. See product data sheet for details regarding the exposed thermal pad dimensions.
- E. Falls within JEDEC MO-229.



DRF (S-PWSON-N8)

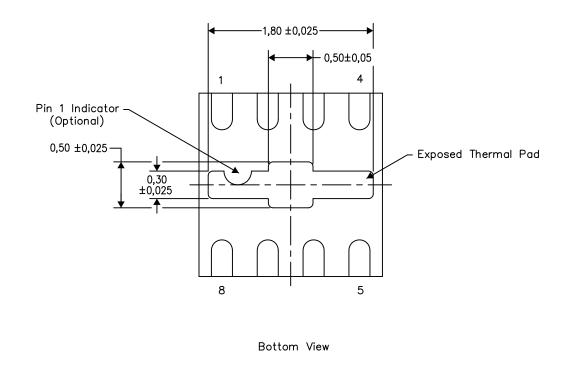
PLASTIC SMALL OUTLINE NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

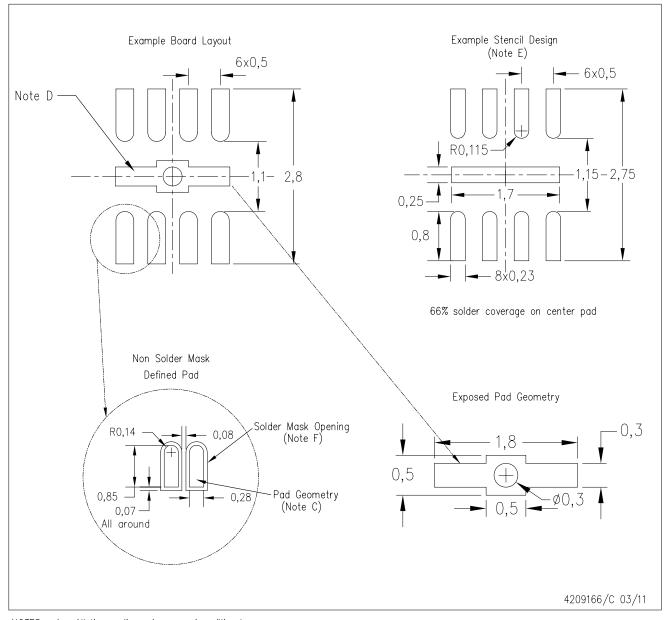
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NOTE: A. All linear dimensions are in millimeters



DRF (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



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